

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	62	memory and magnetic adj memory and write adj line\$1 and write adj circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:12
L2	3	1 and voltage with memory with increas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:17
L3	5	1 and transistor\$1 with independent\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:20
L4	6	1 and transistor\$1 and voltage with increas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:59
L5	3	1 and voltage with memory with increas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:52
L6	11	1 and inverter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:59
L7	8	6 and threshold	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 14:59